

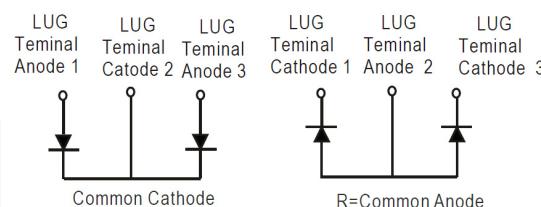
# Low $V_F$ Silicon Power Schottky Diode

 $V_{RRM} = 30 \text{ V}$ 
 $I_{F(AV)} = 600 \text{ A}$ 

## Features

- High Surge Capability
- Type 30 V  $V_{RRM}$
- Isolation Type Package
- Electrically Isolated Base Plate
- Not ESD Sensitive

## Three Tower Package



**Maximum ratings, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

Parameter	Symbol	Conditions	MBRT60030(R)L	Unit
Maximum recurrent peak reverse voltage	$V_{RRM}$		30	V
Maximum RMS voltage	$V_{RMS}$		21	V
Maximum DC blocking voltage	$V_{DC}$		30	V
Operating temperature	$T_j$		-55 to 150	°C
Storage temperature	$T_{stg}$		-55 to 150	°C

**Electrical characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MBRT60030(R)L	Unit
Average forward current (per pkg)	$I_{F(AV)}$	$T_C = 100^\circ\text{C}$	600	A
Peak forward surge current (per leg)	$I_{FSM}$	$t_p = 8.3 \text{ ms, half sine}$	4000	A
Maximum instantaneous forward voltage (per leg)	$V_F$	$I_{FM} = 300 \text{ A, } T_j = 25^\circ\text{C}$	0.58	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	$I_R$	$T_j = 25^\circ\text{C}$ $T_j = 100^\circ\text{C}$	3 250	mA

## Thermal characteristics

Maximum thermal resistance, junction - case (per leg)	$R_{\theta JC}$	0.28	°C/W
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Figure .1-Typical Forward Characteristics

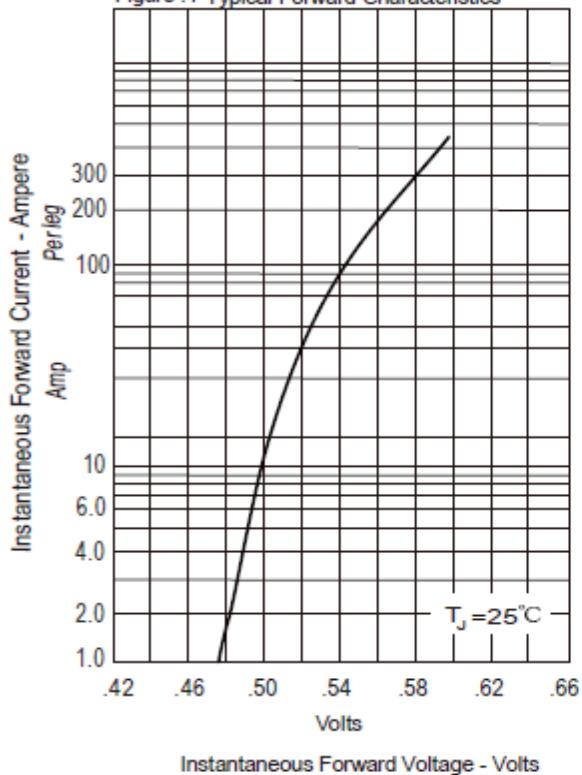


Figure .2-Forward Derating Curve

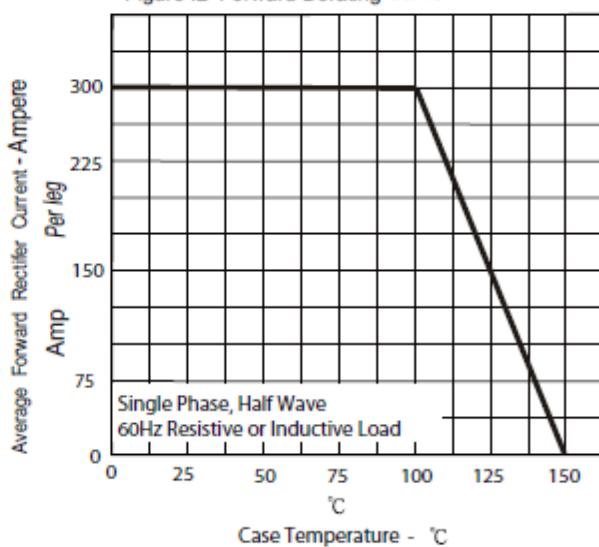


Figure .3-Peak Forward Surge Current

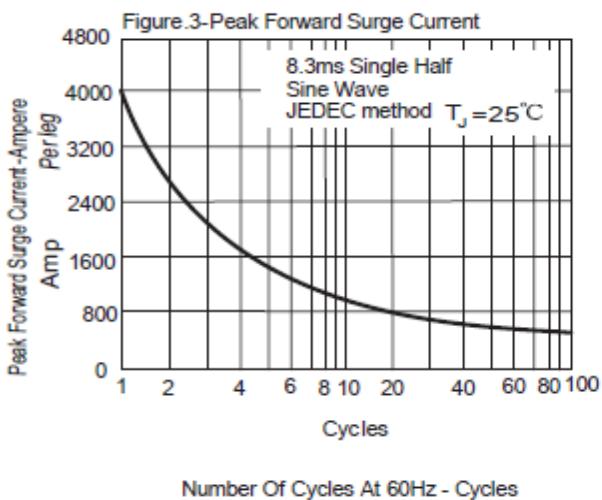
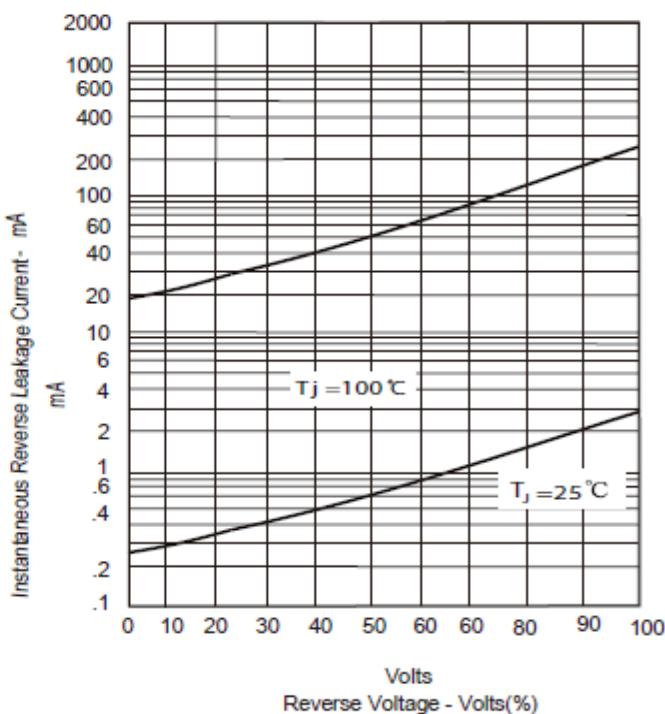
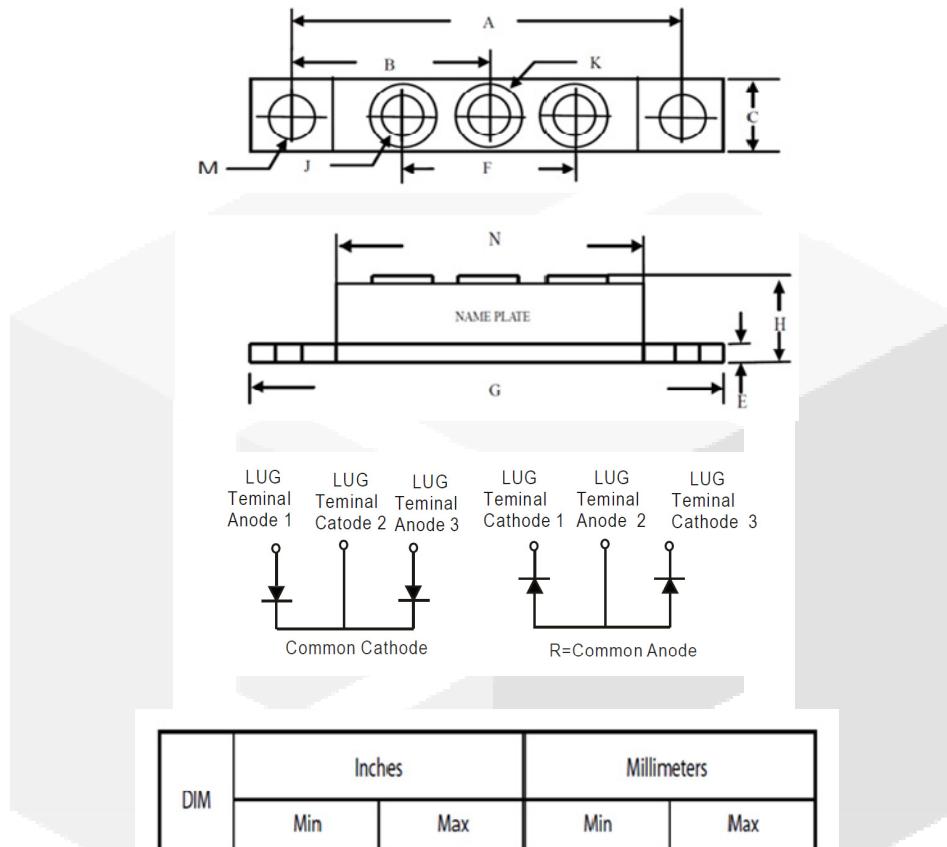


Figure .4-Typical Reverse Characteristics



## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	3.150	NOM	80.01	NOM
B	1.565	1.585	39.75	40.26
C	.700	.800	17.78	20.32
E	.119	.132	3.02	3.35
F	1.327	REF	33.72	REF
G	3.55	3.65	90.17	92.71
H	----	.73	----	18.30
J	1/4-20 UNC FULL			
K	.472	.511	12	13
M	.275	.295	6.99	7.49
N	2.38	2.46	60.5	62.5